Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	2030	361/679	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/22 07:44
L2	14	361/679 and wafer same heat	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/22 08:13
L3	92	(361/679 or 361/696 or 361/697 or 361/701 or 361/702 or 361/709 or 361/711) and wafer same heat	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/22 08:02
L4	529	361/696	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/22 08:06
L5	1570	361/697	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/22 08:08
L6	341	361/701	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/22 08:30
L7	28	(29/888.045 or 29/890.03 or 29/890.032 or 29/890.045 or 29/895.212 or 29/726 or 29/726.5) and wafer same heat	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/22 08:19
L8	1	"6577013".pn. and (insulat$3 or dielectric)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/22 08:19

L9	773	361/702	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/22 08:33
L10	1461	361/709	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/22 08:46
L11	78	electrically near conductive with (crystalline near silicon)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/22 08:40
L12	167	electrically near conductive with (gallium near arsenide)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/22 08:41
L13	390	361/711	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/22 08:50
L14	62	29/888.045	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/22 08:54
L15	1256	29/890.03	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/22 09:03
L16	358	29/890.032	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/22 09:09

L17	179	29/890.045	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/22 09:23
L18	113	29/895.212	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/22 09:32
L19	782	29/726	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/22 09:34
L20	85	29/726.5	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/22 09:34
S1	4	"6710461".pn. or "6624506".pn. or "6501169".pn. or "6492720".pn.	USPAT	OR	OFF	2005/02/22 07:37
S2	11993	wafer and heat near (sink or radiat$3 or dissipat$3 or spread$3 or transfer)	USPAT	OR	ON	2005/02/15 16:59
S3	4300	(semiconductor) near wafer and heat near (sink or radiat$3 or dissipat$3 or spread$3 or transfer)	USPAT	OR	ON	2005/02/15 19:03
S4	338	S3 and stack$3 with wafer	USPAT	OR	ON	2005/02/15 17:53
S5	8	"5,475,215".pn. or "5,604,377".pn. or "5,923,796".pn. or "6,097,857".pn. or "6,230,252".pn. or "6,355,976".pn. or "6,452,705".pn. or "6,611,057".pn.	USPAT	OR	ON	2005/02/15 17:55
S6	283	(semiconductor) near wafer and heat near (sink or radiat$3 or dissipat$3 or spread$3 or transfer) same (coolant or liquor)	USPAT	OR	ON	2005/02/15 20:34
S7	319	S4 not S6	USPAT	OR	ON	2005/02/15 19:03
S8	264	S6 not S4	USPAT	OR	ON	2005/02/15 20:13
S9	14	"4392153"	USPAT	OR	ON	2005/02/15 20:13
S10	4	(semiconductor) near wafer and heat near (sink or radiat$3 or dissipat$3 or spread$3 or transfer) same (coolant or liquor)	JPO	OR	ON	2005/02/15 20:35

S11	18	(semiconductor) near wafer with heat near (sink or radiat$3 or dissipat$3 or spread$3 or transfer) with (alternat$3 or between)	JPO	OR	ON	2005/02/15 20:36
S12	113	(semiconductor) near wafer with heat near (sink or radiat$3 or dissipat$3 or spread$3 or transfer) with (alternat$3 or between)	USPAT	OR	ON	2005/02/15 20:43
S13	28	(semiconductor) near wafer same heat near (sink or radiat$3 or dissipat$3 or spread$3 or transfer) with (side) and (cool$4 or liquor) with heat near (sink or radiat$3 or dissipat$3 or spread$3 or transfer)	USPAT	OR	ON	2005/02/15 20:44
S14	38	(semiconductor) with wafer same heat near (sink or radiat$3 or dissipat$3 or spread$3 or transfer) with (side) and (cool$4 or liquor) with heat near (sink or radiat$3 or dissipat$3 or spread$3 or transfer)	USPAT	OR	ON	2005/02/15 20:50
S15	66	(semiconductor) with wafer and side near heat near (sink or radiat$3 or dissipat$3 or spread$3 or transfer) and (cool$4 or liquor)	USPAT	OR	ON	2005/02/15 21:08
S16	1	"6492720"	USPAT	OR	ON	2005/02/15 21:01
S17	1	"4226281".PN.	USPAT; USOCR	OR	OFF	2005/02/15 21:03
S18	1	"4235283".PN.	USPAT; USOCR	OR	OFF	2005/02/15 21:03
S19	1	"4830456".PN.	USPAT; USOCR	OR	OFF	2005/02/15 21:03
S20	1	"5348214".PN.	USPAT; USOCR	OR	OFF	2005/02/15 21:03
S21	1	"5514852".PN.	USPAT; USOCR	OR	OFF	2005/02/15 21:03
S22	1	"5661639".PN.	USPAT; USOCR	OR	OFF	2005/02/15 21:04
S23	1	"5684675".PN.	USPAT; USOCR	OR	OFF	2005/02/15 21:04
S24	1	"5811877".PN.	USPAT; USOCR	OR	OFF	2005/02/15 21:04
S25	1	"5834843".PN.	USPAT; USOCR	OR	OFF	2005/02/15 21:04
S26	1	"5898575".PN.	USPAT; USOCR	OR	OFF	2005/02/15 21:04
S27	1	"6005290".PN.	USPAT; USOCR	OR	OFF	2005/02/15 21:04

S28	1	"6115242".PN.	USPAT; USOCR	OR	OFF	2005/02/15 21:04
S29	1	"6166437".PN.	USPAT; USOCR	OR	OFF	2005/02/15 21:05
S30	1	"6226776".PN.	USPAT; USOCR	OR	OFF	2005/02/15 21:05
S31	1	"6353264".PN.	USPAT; USOCR	OR	OFF	2005/02/15 21:05
S32	1	"6404048".PN.	USPAT; USOCR	OR	OFF	2005/02/15 21:05
S33	1	"6353264".PN.	USPAT; USOCR	OR	OFF	2005/02/15 21:05
S34	0	(semiconductor) with wafer with cover$3 near side with heat near (sink or radiat$3 or dissipat$3 or spread$3 or transfer) and (coolant or liquor or cooling near water)	USPAT	OR	ON	2005/02/15 21:10
S35	0	cover$3 near side with (semiconductor) with wafer with heat near (sink or radiat$3 or dissipat$3 or spread$3 or transfer) and (coolant or liquor or cooling near water)	USPAT	OR	ON	2005/02/15 21:10
S36	0	cover$3 near side with wafer with heat near (sink or radiat$3 or dissipat$3 or spread$3 or transfer) and (coolant or liquor or cooling near water)	USPAT	OR	ON	2005/02/15 21:10
S37	64	side with wafer with heat near (sink or radiat$3 or dissipat$3 or spread$3 or transfer) and (coolant or liquor or cooling near water)	USPAT	OR	ON	2005/02/15 21:14
S38	1	wafer with heat near (sink or radiat$3 or dissipat$3 or spread$3 or transfer) with alternat$3 with stack$3	USPAT	OR	ON	2005/02/15 21:15
S39	74	wafer with heat near (sink or radiat$3 or dissipat$3 or spread$3 or transfer) with via	USPAT	OR	ON	2005/02/15 21:17
S40	596	wafer with heat near (sink or radiat$3 or dissipat$3 or spread$3 or transfer) and wafer with via	USPAT	OR	ON	2005/02/15 21:18
S41	110	wafer with heat near (sink or radiat$3 or dissipat$3 or spread$3 or transfer) and wafer with via and heat near (sink or radiat$3 or dissipat$3 or spread$3 or transfer) with via	USPAT	OR	ON	2005/02/15 21:25
S42	1009	257/777 and wafer	USPAT	OR	ON	2005/02/15 21:24

S43	137	257/777 and wafer with (via or though near hole)	USPAT	OR	ON	2005/02/15 21:25
S44	50	S43 and wafer and heat near (sink or radiat$3 or dissipat$3 or spread$3 or transfer)	USPAT	OR	ON	2005/02/15 21:39
S45	77	S43 and wafer and heat	USPAT	OR	ON	2005/02/15 21:57
S46	1	"3851221".PN.	USPAT; USOCR	OR	OFF	2005/02/15 21:49
S47	1	"4103318".PN.	USPAT; USOCR	OR	OFF	2005/02/15 21:49
S48	1	"4361261".PN.	USPAT; USOCR	OR	OFF	2005/02/15 21:49
S49	1	"4444349".PN.	USPAT; USOCR	OR	OFF	2005/02/15 21:49
S50	1	"4586642".PN.	USPAT; USOCR	OR	OFF	2005/02/15 21:49
S51	1	"4730232".PN.	USPAT; USOCR	OR	OFF	2005/02/15 21:49
S52	1	"4763188".PN.	USPAT; USOCR	OR	OFF	2005/02/15 21:49
S53	1	"4982265".PN.	USPAT; USOCR	OR	OFF	2005/02/15 21:50
S54	1	"5025306".PN.	USPAT; USOCR	OR	OFF	2005/02/15 21:50
S55	1	"5040052".PN.	USPAT; USOCR	OR	OFF	2005/02/15 21:50
S56	1	"5140404".PN.	USPAT; USOCR	OR	OFF	2005/02/15 21:50
S57	1	"5172215".PN.	USPAT; USOCR	OR	OFF	2005/02/15 21:50
S58	1	"5176311".PN.	USPAT; USOCR	OR	OFF	2005/02/15 21:50
S59	1	"5177032".PN.	USPAT; USOCR	OR	OFF	2005/02/15 21:50
S60	1	"5229647".PN.	USPAT; USOCR	OR	OFF	2005/02/15 21:50
S61	1	"5291060".PN.	USPAT; USOCR	OR	OFF	2005/02/15 21:51
S62	1	"5291061".PN.	USPAT; USOCR	OR	OFF	2005/02/15 21:51
S63	1	"5323060".PN.	USPAT; USOCR	OR	OFF	2005/02/15 21:51
S64	1	"5384689".PN.	USPAT; USOCR	OR	OFF	2005/02/15 21:51
S65	1	"5432729".PN.	USPAT; USOCR	OR	OFF	2005/02/15 21:51

S66	1	"5620928".PN.	USPAT; USOCR	OR	OFF	2005/02/15 21:51
S67	1	"5682062".PN.	USPAT; USOCR	OR	OFF	2005/02/15 21:51
S68	1	"5721452".PN.	USPAT; USOCR	OR	OFF	2005/02/15 21:52
S69	1	"5739581".PN.	USPAT; USOCR	OR	OFF	2005/02/15 21:52
S70	1	"5815372".PN.	USPAT; USOCR	OR	OFF	2005/02/15 21:52
S71	1	"5872025".PN.	USPAT; USOCR	OR	OFF	2005/02/15 21:52
S72	1	"5886412".PN.	USPAT; USOCR	OR	OFF	2005/02/15 21:54
S73	0	"#PATENT#".PN.	USPAT; USOCR	OR	OFF	2005/02/15 21:54
S74	0	"#PATENT#".PN.	USPAT; USOCR	OR	OFF	2005/02/15 21:54
S75	1	"5989982".PN.	USPAT; USOCR	OR	OFF	2005/02/15 21:54
S76	0	"#PATENT#".PN.	USPAT; USOCR	OR	OFF	2005/02/15 21:54
S77	1	"6002163".PN.	USPAT; USOCR	OR	OFF	2005/02/15 21:55
S78	1	"6005778".PN.	USPAT; USOCR	OR	OFF	2005/02/15 21:55
S79	1	"6013948".PN.	USPAT; USOCR	OR	OFF	2005/02/15 21:55
S80	1	"6030855".PN.	USPAT; USOCR	OR	OFF	2005/02/15 21:55
S81	1	"RE36613".PN.	USPAT; USOCR	OR	OFF	2005/02/15 21:55
S82	1	"6033931".PN.	USPAT; USOCR	OR	OFF	2005/02/15 21:55
S83	1	"6051886".PN.	USPAT; USOCR	OR	OFF	2005/02/15 21:55
S84	1	"6057598".PN.	USPAT; USOCR	OR	OFF	2005/02/15 21:55
S85	129	"5229647"	USPAT	OR	ON	2005/02/15 21:57
S86	82	"5229647" and heat	USPAT	OR	ON	2005/02/15 21:57
S87	9	"5229647" and heat with (via or hole)	USPAT	OR	ON	2005/02/15 22:05
S88	3	"6577013" and heat with (via or hole)	USPAT	OR	ON	2005/02/15 22:07

S89	1340	wafer with (via or hole) and heat with (via or hole)	USPAT	OR	ON	2005/02/15 22:08
S90	129	S89 and stack$3 with wafer	USPAT	OR	ON	2005/02/15 22:08
S91	155	wafer with through near (via or open$3 or hole) and heat with through near (via or open$3 or hole)	USPAT	OR	ON	2005/02/16 12:18
S92	422	wafer with through with (via or open$3 or hole) and heat with through with (via or open$3 or hole)	USPAT	OR	ON	2005/02/16 12:25
S93	267	S92 not S91	USPAT	OR	ON	2005/02/16 12:18
S94	1388	wafer with (via or open$3 or hole) and heat with (via or open$3 or hole) and wafer with heat	USPAT	OR	ON	2005/02/16 12:26
S95	3	wafer with (via or open$3 or hole) and heat with (via or open$3 or hole) and wafer with heatsink	USPAT	OR	ON	2005/02/16 12:26
S96	0	wafer with (via or open$3 or hole) and heat with (via or open$3 or hole) and wafer with heatslug	USPAT	OR	ON	2005/02/16 12:26
S97	3	wafer with (via or open$3 or hole) and heat with (via or open$3 or hole) and wafer same heatsink	USPAT	OR	ON	2005/02/16 12:27
S98	170	wafer with (via or open$3 or hole) and heat with (via or open$3 or hole) and wafer same heat near sink	USPAT	OR	ON	2005/02/16 12:40
S99	1716	wafer with (via or open$3 or hole) and heat with (via or open$3 or hole) and wafer same heat	USPAT	OR	ON	2005/02/16 12:40
S100	12	wafer with (via or open$3 or hole) and heat with (via or open$3 or hole) and wafer same heat near spread$3	USPAT	OR	ON	2005/02/16 12:44
S101	1716	wafer with (via or open$3 or hole) and heat with (via or open$3 or hole) and wafer same heat	USPAT	OR	ON	2005/02/16 12:44
S102	1336	S101 not S92	USPAT	OR	ON	2005/02/16 12:44
S103	1	optical near signal with wafer with IC	USPAT	OR	ON	2005/02/16 17:46
S104	0	optical near signal same wafer with IC near optical	USPAT	OR	ON	2005/02/16 17:47
S105	8	optical near signal same (IC or integrated near circuit) near optical and wafer with (IC or integrated near circuit)	USPAT	OR	ON	2005/02/16 18:52

S106	2506	257/712		USPAT	OR	ON	2005/02/16 19:25
S107	1181	257/712		US-PGPUB; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/16 18:54
S108	696	257/685 and heat		US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/16 20:07
S109	1598	257/686 and heat		US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/16 20:07